2SK3269

N-channel enhancement mode MOSFET

■ Features

- Low on-resistance, low Q_g
- High avalanche resistance

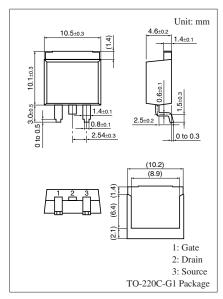
Applications

- For PDP
- For high-speed switching

■ Absolute Maximum Ratings $T_C = 25$ °C

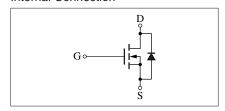
Parameter		Symbol	Rating	Unit	
Drain-source surrender voltage		V_{DSS}	100	V	
Gate-source surrender voltage		V _{GSS}	±20	V	
Drain current		I_{D}	±25	A	
Peak drain current		I_{DP}	±100	A	
Avalanche energy capability *		EAS	22.5	mJ	
Power dissipation		P_{D}	40	W	
	$T_a = 25$ °C		1.4		
Channel temperature		T _{ch}	150	°C	
Storage temperature		T_{stg}	-55 to +150	°C	

Note) *: L = 0.2 mH, $I_L = 15$ A, 1 pulse



Marking Symbol: K3269

Internal Connection



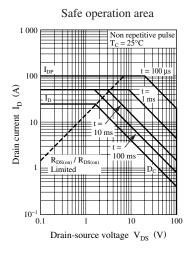
■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

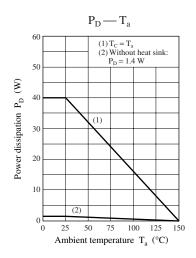
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	100			V
Gate threshold voltage	V _{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0$			10	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$			±1	μΑ
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$		70	100	mΩ
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 12 \text{ A}$	6	11		S
Short-circuit forward transfer capacitance (Common-source)	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		960		pF
Short-circuit output capacitance (Common-source)	C _{oss}			285		pF
Reverse transfer capacitance (Common-source)	C _{rss}			85		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 30 \text{ V}, I_D = 12 \text{ A}$		15		ns
Rise time	T_{r}	$R_{L} = 2.5 \Omega, V_{GS} = 10 V$		10		ns
Turn-off delay time	t _{d(off)}			65		ns
Fall time	t _f			35		ns

■ Electrical Characteristics (continued) $T_C = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode foward voltage	V _{DSF}	$I_{DR} = 15 \text{ A}, V_{GS} = 0$			1.4	V
Thermal resistance (ch-c)	R _{th(ch-c)}				3.125	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				89.3	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.





2 SJG00032AED

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